



F. Silicon and Group-IV Devices and Integration Technology **분과**

2019년 2월 15일(금), 15:30-17:00

Room E (스카이홀, 2층)

**[FE3-F] Advanced Device Technology**

좌장: 조성재 교수(가천대학교), 조일환 교수(명지대학교)

<p><b>FE3-F-1</b> 15:30-15:45</p>	<p><b>Flexible Complementary CNT FETs and Logic Gates by Using Bi-layered Cross-Linked PVA/SU8 Polymers</b> Geon Woong Lim, Seung Yeob Kim, and Sung Hun Jin <i>Department of Electronic Engineering, Incheon National University</i></p>
<p><b>FE3-F-2</b> 15:45-16:00</p>	<p><b>Deep Trench Isolations을 이용한 High Voltage BCD의 Isolations 특성 개선 연구</b> Kiwon Bang, Jaehui Shin, Yonggun Choi, and Sanggi Lee <i>Department of Electronic Engineering, DB HiTek</i></p>
<p><b>FE3-F-3</b> 16:00-16:15</p>	<p><b>Investigation into Reliability Improvement by Double RESURF Optimization in High Voltage PLDMOS</b> Ju-Hee Lee, Joo-Hyung Kim, Seul-Gi Shim, Chun-Hum Cho, and Sang-Gi Lee <i>DB HiTek</i></p>
<p><b>FE3-F-4</b> 16:15-16:30</p>	<p><b>SOI 공정을 이용한 Ron x Coff = 140 fs RF S/W 기술</b> 구자건, 김용진, 김해택, 김현진, 엄승현, 김상길, 임기원, 정진호, 이윤종 <i>DB하이텍 RF/MS파트</i></p>
<p><b>FE3-F-5</b> 16:30-16:45</p>	<p><b>Design and Simulation of Variable Threshold Inverter Using Floating-Gate MOSFET with Independent Double Control-Gate</b> Taehyung Kim, Kyungchul Park, Taejin Jang, Sungmin Hwang, Myung-Hyun Baek, Young Suh Song, and Byung-Gook Park <i>Department of Electrical and Computer Engineering, Seoul National University</i></p>
<p><b>FE3-F-6</b> 16:45-17:00</p>	<p><b>ZnO 절연체의 두께에 따른 Metal-Insulator-Metal 소자의 특성 변화 관찰</b> 이태훈<sup>1</sup>, 정용찬<sup>1</sup>, 성세종<sup>1</sup>, 김선용<sup>1</sup>, 박인성<sup>1,2,3</sup>, 안진호<sup>1,2,3</sup> <sup>1</sup>한양대학교 신소재공학과, <sup>2</sup>한양대학교 나노반도체공학과, <sup>3</sup>한양대학교 나노과학기술연구소</p>